



AS2333

1.8V, MICROPOWER

CMOS ZERO-DRIFT OPERATIONAL AMPLIFIERS

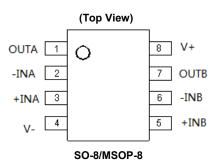
Description

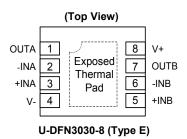
The AS2333 is dual CMOS operational amplifier designed with chopping stabilization technique. This product can provide ultra-low input offset voltage (8µV typical) and near zero-drift over time and temperature. This technique also eliminates 1/f noise and the cross-over distortion present in most rail-to-rail input operational amplifiers. The high-precision, low quiescent current amplifier offers high-impedance inputs that have a common-mode range 100mV beyond the rails, and a rail-to-rail output that swings within 50mV of the rails. Single or dual supplies as low as 1.8V (\pm 0.9V) and up to 5.5V (\pm 2.75V) can be used.

The device is optimized for low voltage single supply application, especially for low-power high-precision applications.

The AS2333 is available in the standard 8-pin SO-8, MSOP-8, and U-DFN3030-8 (Type E) packages, and is specified for operation from -40°C to +125°C.

Pin Assignments





Features

- Low Input Offset Voltage: 8µV (typ)
- Zero Drift: 0.02µV/°C (typ)
- 0.01Hz to 10Hz Noise: $1.1 \mu V_{PP}$
- Low Quiescent Current: 12µA per Amplifier
- Supply Voltage: 1.8V to 5.5V
- Rail-to-Rail Input and Output
- Bandwidth 350kHz

Notes:

- Slew Rate 0.12V/µs (typ)
- MSOP-8, SO-8, and U-DFN3030-8 (Type E) Packages
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

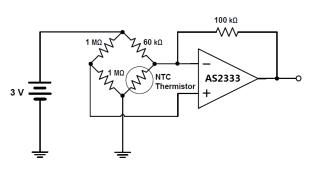
Applications

- Battery-Powered Instruments
- Handheld Test Equipment
- Medical Instrumentation
- Sensor Signal Conditioning
- Low Voltage Current Sensing

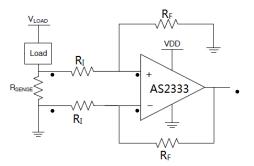
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Typical Application



Thermistor Measurement



Low-Side Current Monitor

Pin Descriptions

Pin Number	Pin Name	I/O	Description
3	+INA	I	Noninverting input, channel A
5	+INB	I	Noninverting input, channel B
2	-INA	I	Inverting input, channel A
6	-INB	I	Inverting input, channel B
1	OUTA	0	Output, channel A
7	OUTB	0	Output, channel B
8	V+	_	Positive Power Supply Recommend to place a minimum 0.1µF decoupling capacitor between V+ pin and GND as close as possible.
4	V-	_	Negative Power Supply Single power supply application, it is normally tied to ground. Split power supply application, a minimum 0.1µF decouple capacitor is recommended to be placed between V- pin and GND as close as possible.



Or much a l	Descusation	Rating		11-14
Symbol	Parameter			Unit
$V_{\rm S}$ = V+ - V-	Supply Voltage Range	6.5		V
V _{-IN} / V _{+IN}	Signal Input Terminals (Note 5)	V 0.3V to V+	+ 0.3V	V
	Signal Input Terminals (Note 5)	-1 to +1		mA
	Output Short-Circuit (Note 6)	Continuo	JS	mA
T _{STG}	Storage Temperature	-65 to +1	50	°C
TJ	Maximum Junction Temperature	+150		°C
T _{LEAD}	Lead Temperature (Soldering, 10 Seconds)	+260		°C
	Junction-to-Ambient Thermal Resistance	SO-8	139	°C/W
$R_{ extsf{ heta}JA}$		MSOP-8	184	°C/W
		U-DFN3030-8 (Type E)	_	°C/W
		SO-8	25	°C/W
$R_{ extsf{ heta}JC}$	Junction-to-Case Thermal Resistance	MSOP-8	18	°C/W
		U-DFN3030-8 (Type E)	_	°C/W
ESD HBM	Human Body Model ESD Protection	4		kV
ESD CDM	Charged-Device Model ESD Protection	1		kV

Absolute Maximum Ratings (Note 4) (@ T_A = +25°C, unless otherwise specified.)

Notes: 4. Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Recommended Operating Conditions indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications and the test conditions, see the Electrical Characteristics.

5. Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.3V beyond the supply rails should be current limited to 10mA or less.

6. Short-circuit to ground.

Recommended Operating Conditions (@ T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Rating	Unit
V _S = V+ - V-	Supply Voltage Range	1.8 to 5.5	V
TA	Operating Ambient Temperature Range	-40 to +125	°C



Electrical Characteristics (@ $T_A = +25^{\circ}C$, $V_S = 5.0V$, $R_L = 10k\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$, unless otherwise specified.)

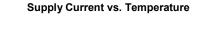
Symbol	Parameter	Cor	nditions	Min	Тур	Мах	Unit
Offset Voltag	e	1					
V _{OS}	Input Offset Voltage	V _S = 5V		_	8	22	μV
		T _A = -40°C to +8	5°C	—	0.02	0.1	μV/°C
$\Delta V_{OS} / \Delta T$	Input Offset Voltage Drift (Note 7)	T _A = -40°C to +125°C		_		0.2	μV/°C
PSRR	Power-Supply Rejection Ratio	V _S = 1.8V to 5.5' +125°C		_	1	5	μV/V
_	Long-Term Stability		_		(Note 7)		μV
_	Channel Separation, DC		_	_	0.1	_	μV/V
Input Bias Cu	irrent						
		T _A = +25°C		_	±70	±200	
IB	Input Bias Current	T _A = -40°C to +1	25°C	—	±400	_	pА
los	Input Offset Current		_	_	±140	±400	
Noise	P				-		
		f = 0.01Hz to 1H	Z	_	0.3	_	
V _N	Input Voltage Noise	f = 0.1Hz to 10H		_	1.1	_	μV _{PP}
IN	Input Current Noise	f = 10Hz			100	_	fA/√Hz
Input Voltage							
V _{CM}	Common-Mode Voltage Range		_	(V-) - 0.1		(V+) + 0.1	V
CMRR	Common-Mode Rejection Ratio	$(V-) - 0.1V < V_{CM} < (V+) + 0.1V,$ $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		106	120		dB
Input Capacit	ance						
_	Differential		_		2	_	pF
	Common-Mode		_	_	4	_	pF
Open-Loop G	ain						
A _{OL}	Open-Loop Voltage Gain		$(V-) + 100mV < V_O < (V+) - 100mV,$ $R_L = 10k\Omega, T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		130	_	dB
Frequency Re	esponse						
GBW	Gain-Bandwidth Product	C _L = 100pF		_	350	_	kHz
SR	Slew Rate	G = +1		_	0.12	_	V/µs
Output	1	I.					
		Positive Rail	T _A = +25°C	_	30	50	
		$R_L = 10k\Omega$	T _A = -40°C to +125°C	_		70	
_	Voltage Output Swing from Rail	Negetice Dell	T _A = +25°C	_	10	50	mV
		Negative Rail R _L = 10kΩ	T _A = -40°C to +125°C	_	_	70	1
			Source Current		5	_	mA
Isc	Short-Circuit Current	Sink Current		_	25	_	mA
_	Open-Loop Output Impedance	f = 350kHz, I _O = 0A		—	2	—	kΩ
Power Supply	<u> </u>	1					
Vs	Specified Voltage Range					5.5	V
		I _O = 0A, T _A = +2	5°C	_	12	20	-
lq	Quiescent Current per Amplifier	$I_0 = 0A, T_A = -40^{\circ}C \text{ to } +125^{\circ}C$				28	μA
· Q		$V_{\rm S} = 5V$				20	

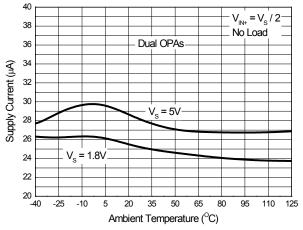
Note:

7. 300-hour life test at +150°C demonstrated randomly distributed variation of approximately 1 μ V. This parameter guaranteed by design and characterization, not by testing.

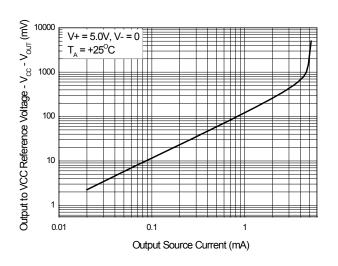


Typical Performance Characteristics

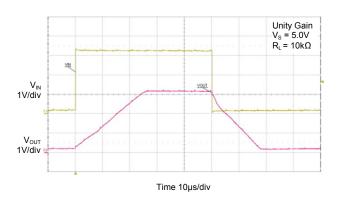




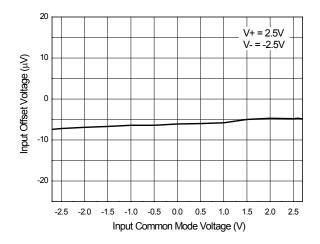
Output Characteristics-Sourcing Current



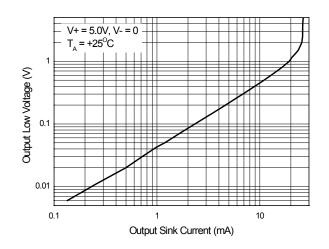
Large Signal Response



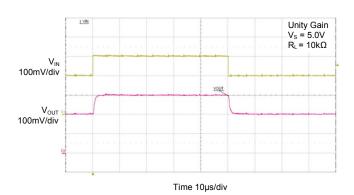
Input Offset Voltage vs. Input Common Mode Voltage



Output Characteristics-Sinking Current

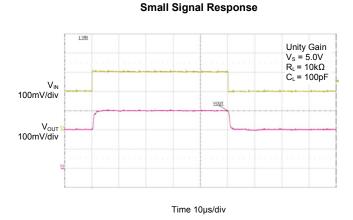


Small Signal Response





Typical Performance Characteristics (continued)

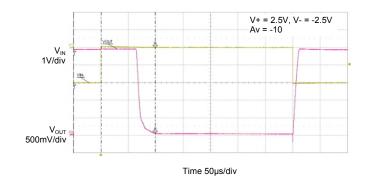


VIN Unity Gain VIN V_S = 5.0V 100mV/div C_L = 220pF

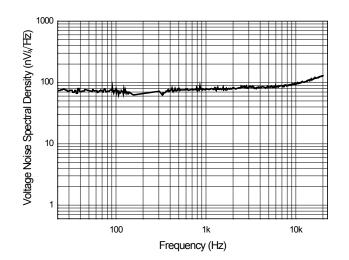
Time 10µs/div

Small Signal Response

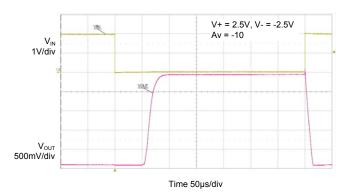
Positive Overvoltage Response



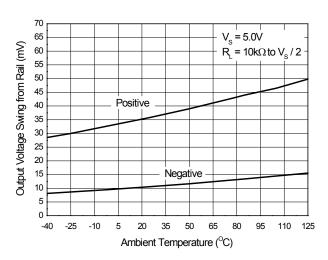
Voltage Noise Spectral Density



Negative Overvoltage Response

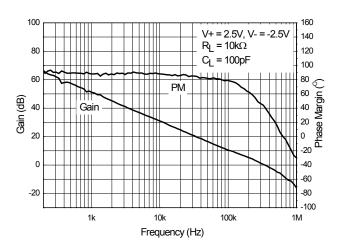


Output Voltage Swing from Rail



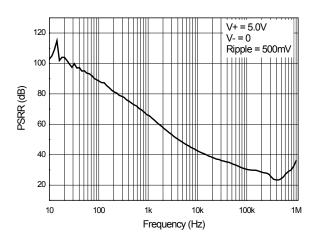


Typical Performance Characteristics (continued)



Frequency Response

Power Supply Rejection Ration vs. Frequency





Application Information

Overview

The AS2333 is low-power, zero-drift, high-precision, rail-to-rail input and output operational amplifier, which adopts chopper-stabilized function circuits to provide the advantage of minimizing input offset voltage and offset voltage drift over time and temperature. Its input common-mode voltage range extends 0.1V beyond the supply rails to allow for sensing near ground or system V_{DD}. The device operates from a single-supply voltage as low as 1.8V, is unity-gain stable, has no 1/f noise, and has good PSRR and CMRR performance. These features make the AS2333 suitable for a wide range of general-purpose applications, especially for low-power and high-precision applications.

Low Input Referred Noise

The device AS2333 is chopper-stabilized amplifier, which greatly reduces the flicker noise. The zero-drift chopper-stabilized amplifiers are especially suited for accurate, high-gain amplification at lower frequencies. In general, they do not exhibit the higher bandwidth of linear operational amplifiers, and the location of their clock frequency establishes a practical frequency limit on signal fidelity. This makes performance at low frequencies especially important, and the chopper-stabilized architecture further contributes to low-frequency usefulness by eliminating the classic linear operational amplifier 1/f input voltage noise. Many high-gain sensor applications are at low frequencies, making zero-drift amplifiers a natural choice for this function.

The below graphs compare the voltage noise density behaviors of conventional amplifiers and zero-drift amplifiers. The 1/f noise elimination in zero-drift amplifiers allow the AS2333 to have much lower noise at DC and low frequencies compared to the conventional low-noise amplifiers.

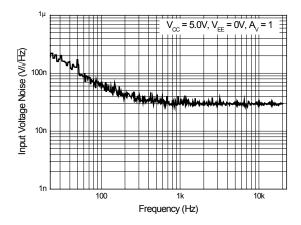
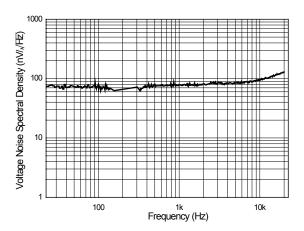


Figure 1. Input Voltage Noise in Conventional Amplifier (AZV832)





Driving a Capacitive Load

The AS2333 can directly drive 200pF in unity-gain without oscillation. The unity-gain follower is the most sensitive configuration to capacitive loading. Capacitive loading directly on the output terminal can decrease the device's phase margin, leading to high-frequency ringing or oscillation.

To drive a heavier capacitive load, the circuit in Figure 3 can be used. The resistor R_{NULL} and C_L form a pole to increase stability by adding more phase margin to the system. The bigger the R_{NULL} resistor value, the more stable V_{OUT} is. Figure 4 and Figure 5 show the AS2333's output pulse response waveforms with and without R_{NULL} 330 Ω for load conditions C_L = 470pF and R_L = 10k Ω .



Application Information (continued)

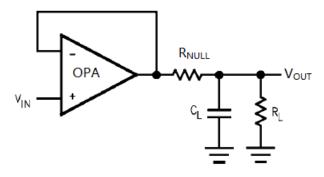


Figure 3. Capacitive Load with RNULL

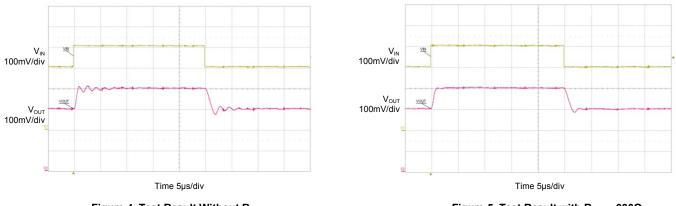


Figure 4. Test Result Without R_{NULL}

Figure 5. Test Result with R_{NULL} 330 Ω

An RC snubber circuit can be used to reduce capacitive load ringing and overshoot, as shown in Figure 6. It allows the amplifier to drive larger values of capacitance while maintaining a minimum for overshoot and ringing. Figure 7 shows AS2333's test results for capacitive load 470pF with a snubber circuit.

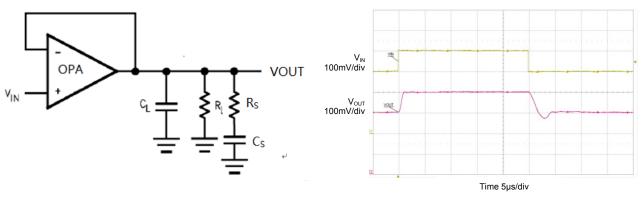


Figure 6. Circuit with Snubber Circuit

Figure 7. Test Result with Snubber Circuit



Application Information (continued)

Low-Side Current Monitor Application

Low-side current sensing is used to monitor the current through a load. This method can be used to detect over-current conditions and is often used in feedback control, as shown in Figure 8. A sense resistor is placed in series with the load to the ground. Precision resistors are required for high accuracy and the resulting voltage drop is amplified using the AS2333.

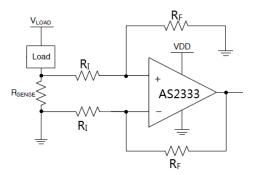


Figure 8. Low-Side Current Monitor Application

Differential Amplifier for Bridged Circuits

Sensors to measure strain, pressure, and temperature are often configured in a Wheatstone bridge circuit, as shown in Figure 9. In the measurement, the voltage change that is produced is relatively small and needs to be amplified before going into an ADC. Precision amplifiers are recommended in these types of applications due to their high gain, low noise, and low offset voltage.

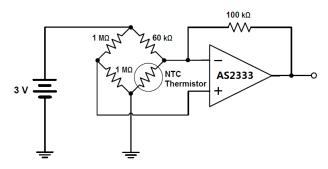
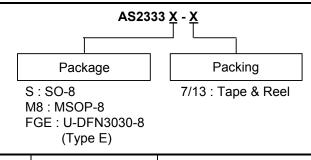


Figure 9. Bridge Circuit Amplification



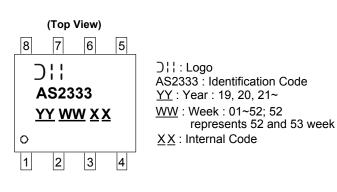
Ordering Information



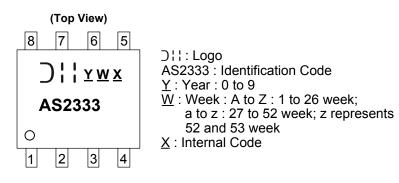
Part Number	Identification	Paakaging	Tape a	Tape and Reel	
Fart Nulliger	Code	Packaging	Quantity	Part Number Suffix	
AS2333S-13	AS2333	SO-8	2500/Tape & Reel	-13	
AS2333M8-13	AS2333	MSOP-8	2500/Tape & Reel	-13	
AS2333FGE-7	ND	U-DFN3030-8 (Type E)	3000/Tape & Reel	-7	

Marking Information

(1) SO-8



(2) MSOP-8



(3) U-DFN3030-8 (Type E)

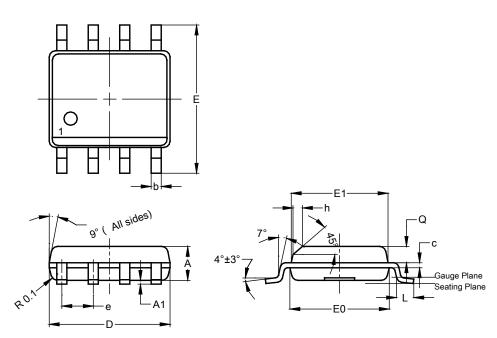
(Top View)	
<u>ND</u> ⊻₩X ●	ND : Identification Code <u>Y</u> : Year : 0~9 <u>W</u> : Week : A~Z : 1~26 week; a~z : 27~52 week; z represents 52 and 53 week X : Internal Code



Package Outline Dimensions

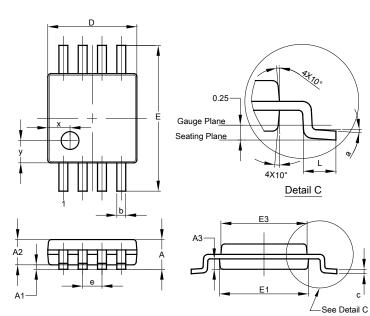
Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: SO-8



	SO-8				
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е			1.27		
h			0.35		
L	0.62	0.82	0.72		
Q	0.60	0.70	0.65		
All	Dimens	ions in	mm		

(2) Package Type: MSOP-8



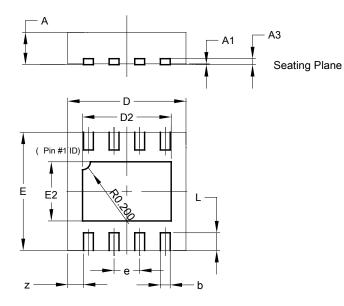
MSOP-8				
Dim	Min	Max	Тур	
Α	-	1.10	-	
A1	0.05	0.15	0.10	
A2	0.75	0.95	0.86	
A3	0.29	0.49	0.39	
b	0.22	0.38	0.30	
С	0.08	0.23	0.15	
D	2.90	3.10	3.00	
Е	4.70	5.10	4.90	
E1	2.90	3.10	3.00	
E3	2.85	3.05	2.95	
e	-	1	0.65	
1	0.40	0.80	0.60	
а	0°	8°	4°	
Х	-	-	0.750	
у	-	-	0.750	
All D	Dimen	sions	in mm	



Package Outline Dimensions (continued)

Please see http://www.diodes.com/package-outlines.html for the latest version.

(3) Package Type: U-DFN3030-8 (Type E)



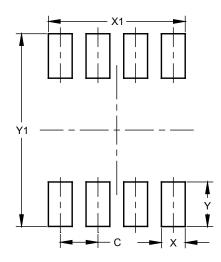
U-DFN3030-8					
	(Ту	pe E)			
Dim	Min	Max	Тур		
Α	0.57	0.63	0.60		
A1	0.00	0.05	0.02		
A3	-	-	0.15		
b	0.20	0.30	0.25		
D	2.95	3.05	3.00		
D2	2.15	2.35	2.25		
Е	2.95	3.05	3.00		
E2	1.40	1.60	1.50		
е	-	-	0.65		
L	0.30	0.60	0.45		
z	-	-	0.40		
All	Dimen	sions in	mm		



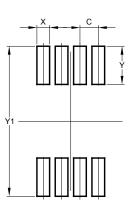
Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

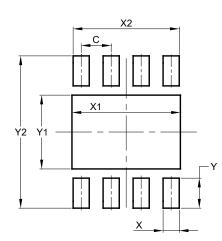
(1) Package Type: SO-8



(2) Package Type: MSOP-8



(3) Package Type: U-DFN3030-8 (Type E)



Value (in mm)
1.27
0.802
4.612
1.505
6.50

Dimensions	Value (in mm)
C	0.650
Х	0.450
Y	1.350
Y1	5.300

Dimensions	Value (in mm)
C	0.650
Х	0.350
X1	2.350
X2	2.300
Y	0.650
Y1	1.600
Y2	3.300



Mechanical Data

SO-8

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.075 grams (Approximate)

MSOP-8

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.025 grams (Approximate)

U-DFN3030-8 (Type E)

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Lead-Frame Solderable per MIL-STD-202, Method 208 4
- Weight: 0.017 grams (Approximate)



IMPORTANT NOTICE

1. DIODES INCORPORATED AND ITS SUBSIDIARIES ("DIODES") MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes products. Diodes products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of the Diodes products for their intended applications, (c) ensuring their applications, which incorporate Diodes products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.

3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes' websites, harmless against all damages and liabilities.

4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes' website) under this document.

provided Diodes products are subject to Diodes' Standard Terms and Conditions of Sale (https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.

6. Diodes products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.

7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.

8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.

Copyright © 2021 Diodes Incorporated

www.diodes.com